

**PATENT APPLICATION**  
Attorney Docket No.: 2000.010.00/US

PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT FORM PTO-1449 (Modified)</b> (USE AS MANY SHEETS AS NECESSARY)				<b>Complete if Known</b>	
SHEET	1	OF	2	Application Number	
				Filing Date	
				First Named Inventor	Farid Nemati
				Art Unit	
				Examiner Name	
				Attorney Docket Number	2000.010.00/US

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number- Kind Code (if known)			
P D		US 6,229,161 ✓	05-08-01	Nemati et al.	
✓		US 6,448,586 ✓	09-10-02	Nemati et al.	
		US 6,462,359 ✓	10-08-02	Nemati et al.	
		US 6,528,356 ✓	03-04-03	Nemati et al.	
		US 5,448,104 ✓	09-05-95	Yallup	
		US-5,627,401 ✓	05-06-97	Yallup	
		US-4,965,872 ✓	10-23-90	Vasudev	
		US-6,492,662 ✓	12-10-02	Hsu, et al.	
		US-6,512,274 ✓	01-28-03	King, et al.	
		US-6,545,297 ✓	04-08-03	Noble, Jr., et al.	
		US-6,552,398 ✓	04-22-03	Hsu, et al.	
		US-6,583,452 ✓	06-24-03	Cho, et al.	
✓		US-6,611,452 ✓	08-26-03	Han	
P D		US-6,627,924 ✓	09-30-03	Hsu, et al.	

FOREIGN PATENT DOCUMENTS					
Examiner Initials	Cite No.1	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code3-Number4 - Kind Code 5 (if known)			

Examiner Signature	PHUC T. DANG	Date Considered	5/5/2005
--------------------	--------------	-----------------	----------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.

**PATENT APPLICATION**  
Attorney Docket No.: 2000.010.00/US

PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <b>FORM PTO-1449 (Modified)</b> <i>(USE AS MANY SHEETS AS NECESSARY)</i>				<b>Complete if Known</b>	
SHEET	2	OF	2	Application Number	
				Filing Date	
				First Named Inventor	Farid Nemati
				Art Unit	
				Examiner Name	
				Attorney Docket Number	2000.010.00/US

<b>OTHER PRIOR ART – LITERATURE DOCUMENTS</b>					
Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T2
P D ↑		FARID NEMATI et al., U.S. Pat. Appl. Ser. No. 10/706,162, filed Nov. 12, 2003, <i>Thyristor Circuit and Approach for Temperature Stability</i> , assigned to the assignee of the present application. C-028			
		F.NEMATI and J.D. PLUMMER, <i>A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device</i> , VLSI Technology Technical Digest, 1998.			
		F.NEMATI and J.D. PLUMMER, <i>A Novel Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-Scale Memories</i> , International Electron Device Meeting Technical Digest 1999.			
		NATIONAL SCIENTIFIC CORP., <i>TMOS Memory Cell, Breakthrough Technology in SRAM</i> , at <a href="http://www.nsclocators.com/images/pdf/1P_tmos-2003.PDF">http://www.nsclocators.com/images/pdf/1P_tmos-2003.PDF</a> , 2003.			
↓ P D		R.COLIN JOHNSON, <i>Hybrid Tunnel Diodes Could Leapfrog Moore's Law</i> , EE Times, October 29, 2003, also at <a href="http://www.eetimes.com/at/news/OEG20031029S0015">www.eetimes.com/at/news/OEG20031029S0015</a> .			

Examiner Signature	PHUONG T. DANG	Date Considered	5/5/2005
--------------------	----------------	-----------------	----------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.